

ABSTRACT

Disclosed herein is a wafer producing method for producing an SiC wafer from a single crystal SiC ingot. The wafer producing method includes a separation surface forming step of forming a separation surface composed of modified layers, cracks, and connection layers inside the ingot and a wafer separating step of separating a part of the ingot along the separation surface as an interface to thereby produce the wafer. The separation surface forming step includes a modified layer forming step of forming the modified layers and the cracks extending from the modified layers along a c-plane, and a connection layer forming step of forming the connection layers each connecting the cracks formed adjacent to each other in the thickness direction of the ingot.

[Figure 5C]